

# **4V Drive Nch MOSFET**

# RSD080N06

#### Structure

Silicon N-channel MOSFET

#### ● Features

- 1) Low on-resistance.
- 2) 4V drive.
- 3) High power package(CPT3).

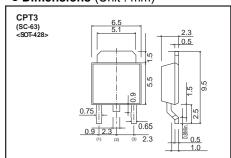
## Application

Switching

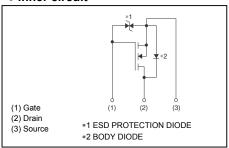
Packaging specifications

	Package	Taping	
Type	Code	TL	
	Basic ordering unit (pieces)	2500	
RSD080N0	0		

#### Dimensions (Unit : mm)



#### • Inner circuit



# ● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		$V_{DSS}$	60	V
Gate-source voltage		$V_{GSS}$	±20	V
Drain current	Continuous	I <sub>D</sub>	<u>±</u> 8	Α
	Pulsed	I <sub>DP</sub> *1	±16	Α
Source current	Continuous	I <sub>S</sub>	8	Α
(Body Diode)	Pulsed	I <sub>SP</sub> *1	16	Α
Power dissipation		P <sub>D</sub> *2	15	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

<sup>\*1</sup> Pw $\leq$ 10 $\mu$ s, Duty cycle $\leq$ 1%

#### • Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to Case	Rth (ch-c)*	8.33	°C / W

<sup>\*</sup> T<sub>C</sub>=25°C

<sup>\*2</sup> T<sub>C</sub>=25°C

## ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	-	-	±10	μA	$V_{GS}=\pm20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	1	ı	>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	1	-	1	μA	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	1.0	-	2.5	٧	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA
Otatia dualin annua an atata	*	1	57	80		I <sub>D</sub> =8A, V <sub>GS</sub> =10V
Static drain-source on-state resistance	R <sub>DS (on)</sub>	1	70	98	mΩ	I <sub>D</sub> =8A, V <sub>GS</sub> =4.5V
redictarioe		-	78	109		I <sub>D</sub> =8A, V <sub>GS</sub> =4.0V
Forward transfer admittance	I Y <sub>fs</sub> I*	4.8	-	-	S	V <sub>DS</sub> =10V, I <sub>D</sub> =8A
Input capacitance	C <sub>iss</sub>	ı	380	-	pF	V <sub>DS</sub> =10V
Output capacitance	C <sub>oss</sub>	-	90	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>	1	50	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	1	9	-	ns	V <sub>DD</sub> ≒ 30V, I <sub>D</sub> =4A
Rise time	t <sub>r</sub> *	1	13	-	ns	V <sub>GS</sub> =10V
Turn-off delay time	t <sub>d(off)</sub> *	ı	30	-	ns	$R_L$ =7.5 $\Omega$
Fall time	t <sub>f</sub> *	-	10	-	ns	$R_G$ =10 $\Omega$
Total gate charge	Q <sub>g</sub> *	-	9.4		nC	V <sub>DD</sub> ≒ 30V, I <sub>D</sub> =8A
Gate-source charge	Q <sub>gs</sub> *	-	1.8	-	nC	V <sub>GS</sub> =10V
Gate-drain charge	Q <sub>gd</sub> *	-	2.3	-	nC	

<sup>\*</sup>Pulsed

# ●Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V <sub>SD</sub> *	-	-	1.5	V	I <sub>s</sub> =8A, V <sub>GS</sub> =0V

<sup>\*</sup>Pulsed

8

6

2

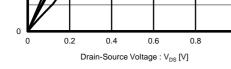
Drain Current: I<sub>D</sub> [A]

#### ●Electrical characteristic curves (Ta=25°C)

T<sub>a</sub>=25°C pulsed

V<sub>GS</sub>=3.0V

Fig.1 Typical Output Characteristics ( I )



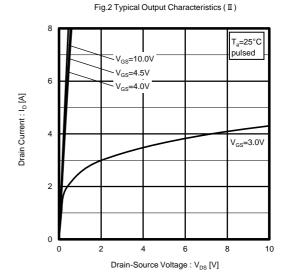
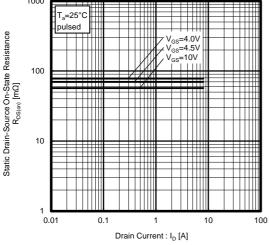


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current





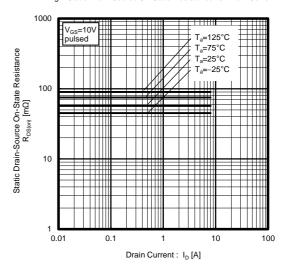
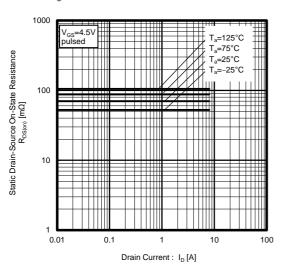


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current





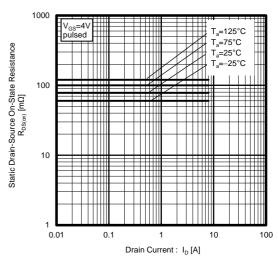
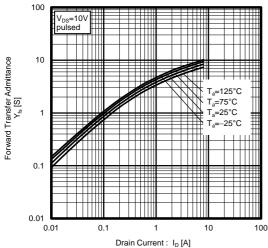


Fig.7 Forward Transfer Admittance vs. Drain Current



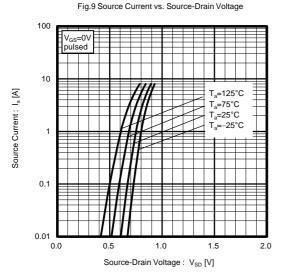


Fig.11 Switching Characteristics

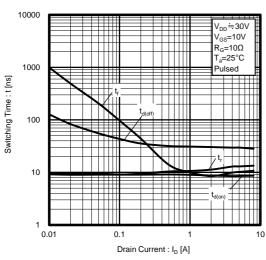


Fig.8 Typical Transfer Characteristics

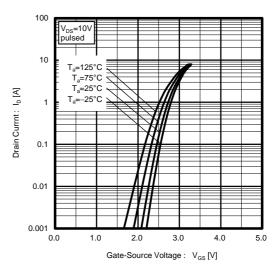


Fig.10 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

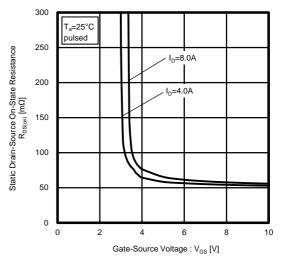


Fig.12 Dynamic Input Characteristics

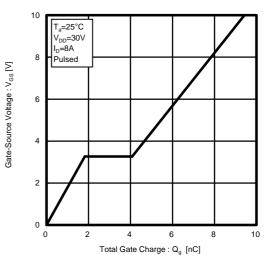


Fig.13 Typical Capacitance vs. Drain-Source Voltage

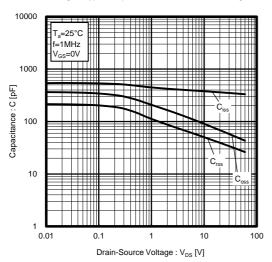


Fig.15 Normalized Transient Thermal Resistance v.s. Pulse Width

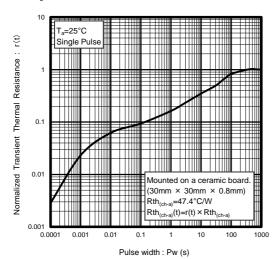
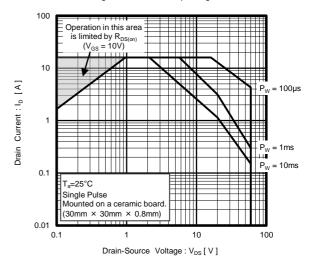


Fig.14 Maximum Safe Operating Area



#### Measurement circuits

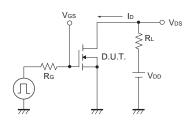


Fig.1-1 Switching Time Measurement Circuit

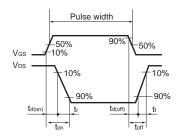


Fig.1-2 Switching Waveforms

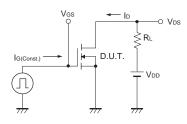


Fig.2-1 Gate Charge Measurement Circuit

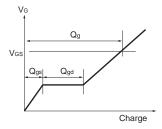


Fig.2-2 Gate Charge Waveform

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